

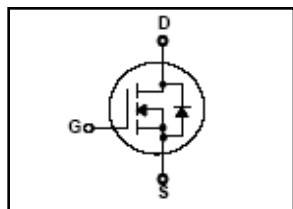
HCS65R180S

650V N-Channel Super Junction MOSFET

$BV_{DSS} = 650\text{ V}$
 $R_{DS(on) \text{ typ}} = 0.15\ \Omega$
 $I_D = 20\text{ A}$

FEATURES

- Originative New Design
- Superior Avalanche Rugged Technology
- Robust Gate Oxide Technology
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge : 46 nC (Typ.)
- Extended Safe Operating Area
- Lower $R_{DS(ON)}$: 0.15 Ω (Typ.) @ $V_{GS}=10\text{V}$
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current – Continuous ($T_C = 25^\circ\text{C}$)	20 *	A
	Drain Current – Continuous ($T_C = 100^\circ\text{C}$)	10 *	A
I_{DM}	Drain Current – Pulsed (Note 1)	60 *	A
V_{GS}	Gate-Source Voltage	Static	± 20
		AC ($f > 1\text{ Hz}$)	± 30
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	710	mJ
I_{AR}	Avalanche Current (Note 1)	20	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	1	mJ
dv/dt	Peak Diode Recovery dv/dt	15	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	45	W
		0.36	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	2.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient	--	60.5	

Electrical Characteristics $T_J=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.8	--	4.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\ \text{V}, I_D = 10\ \text{A}$	--	0.15	0.18	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\ \text{V}, I_D = 250\ \mu\text{A}$	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\ \text{V}, V_{GS} = 0\ \text{V}$	--	--	10	μA
		$V_{DS} = 520\ \text{V}, T_J = 125\text{ }^\circ\text{C}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$	--	--	± 100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\ \text{V}, V_{GS} = 0\ \text{V},$ $f = 1.0\ \text{MHz}$	--	1850	--	pF
C_{oss}	Output Capacitance		--	500	--	pF
C_{rss}	Reverse Transfer Capacitance		--	9	--	pF
R_g	Gate Resistance	$V_{GS} = 0\ \text{V}, V_{DS} = 0\ \text{V}, f = 1\ \text{MHz}$	--	0.54	--	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	$V_{DS} = 325\ \text{V}, I_D = 20\ \text{A},$ $R_G = 25\ \Omega$	--	45	--	ns
t_r	Turn-On Rise Time		--	40	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	140	--	ns
t_f	Turn-Off Fall Time		--	25	--	ns
Q_g	Total Gate Charge	$V_{DS} = 520\ \text{V}, I_D = 20\ \text{A}$ $V_{GS} = 10\ \text{V}$	--	46	--	nC
Q_{gs}	Gate-Source Charge		--	12	--	nC
Q_{gd}	Gate-Drain Charge		--	16	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	20	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	60	
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 20\ \text{A}, V_{GS} = 0\ \text{V}$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = 10\ \text{A}, V_{GS} = 0\ \text{V}$ $di_F/dt = 100\ \text{A}/\mu\text{s}$	--	330	--	ns
Q_{rr}	Reverse Recovery Charge		--	3.8	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS}=6\text{A}, V_{DD}=50\text{V}, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$

Typical Characteristics

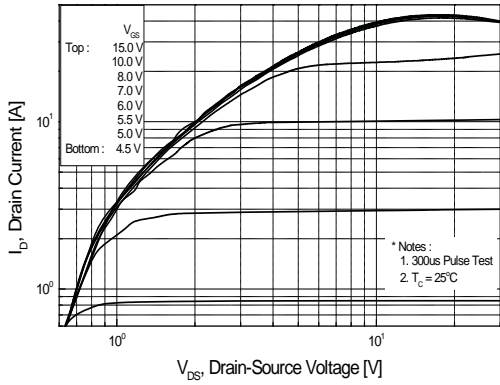


Figure 1. On Region Characteristics

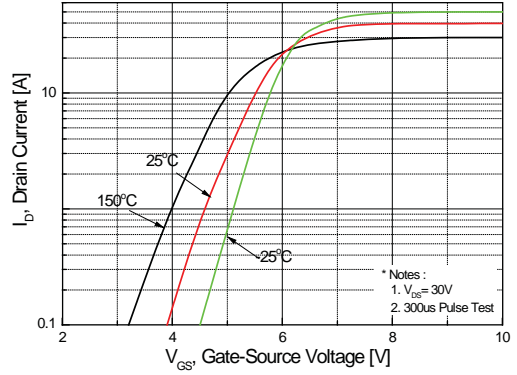


Figure 2. Transfer Characteristics

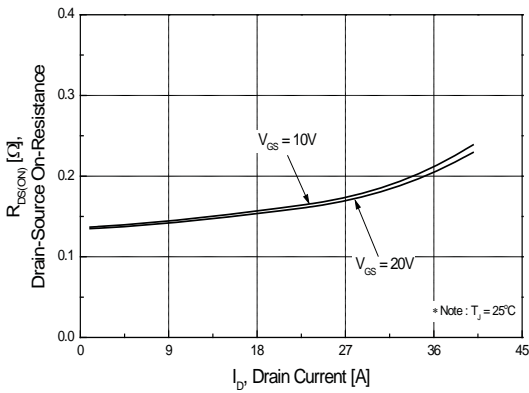


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

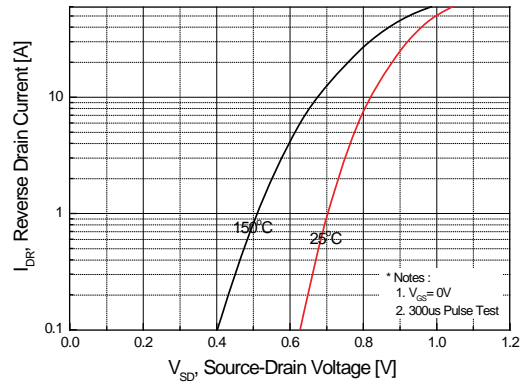


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

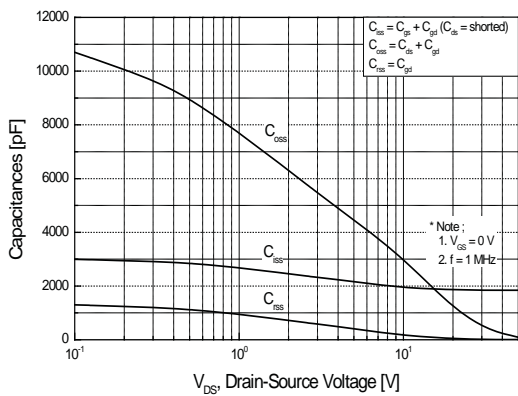


Figure 5. Capacitance Characteristics

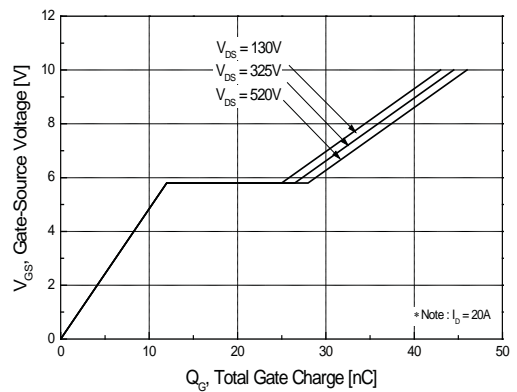


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

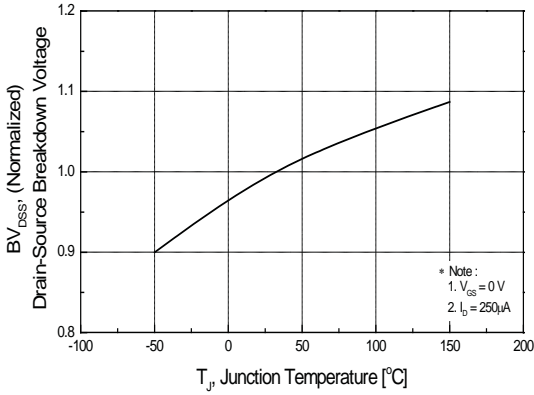


Figure 7. Breakdown Voltage Variation vs Temperature

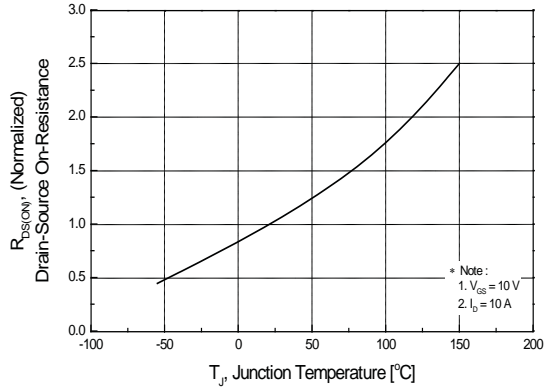


Figure 8. On-Resistance Variation vs Temperature

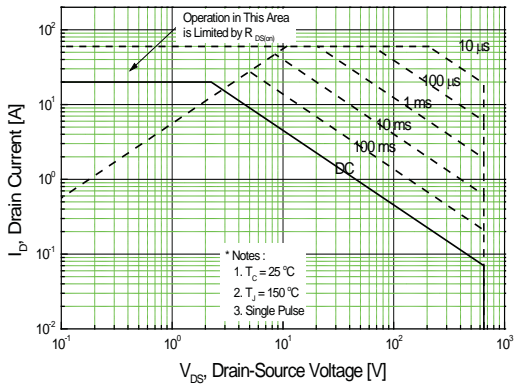


Figure 9. Maximum Safe Operating Area

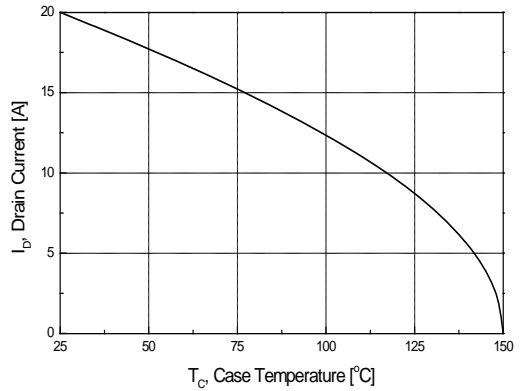


Figure 10. Maximum Drain Current vs Case Temperature

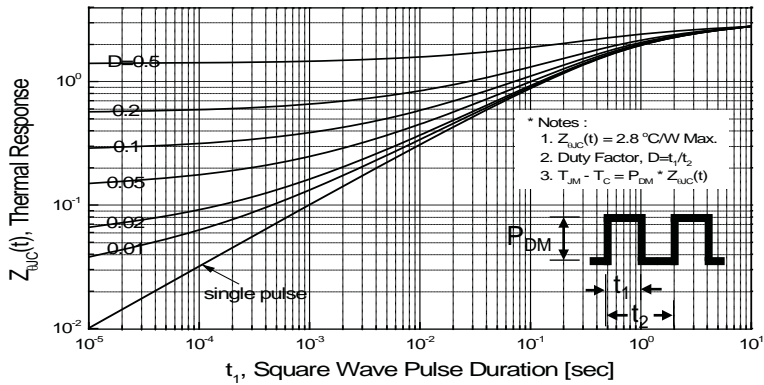


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform



Fig 13. Resistive Switching Test Circuit & Waveforms



Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

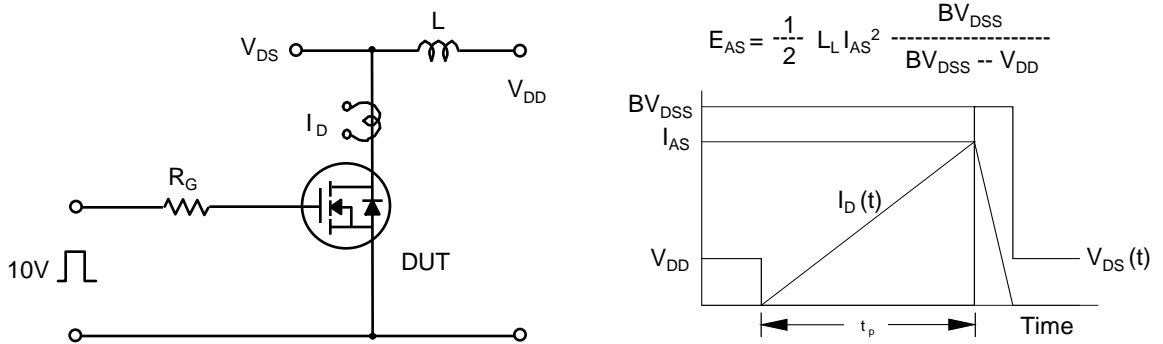
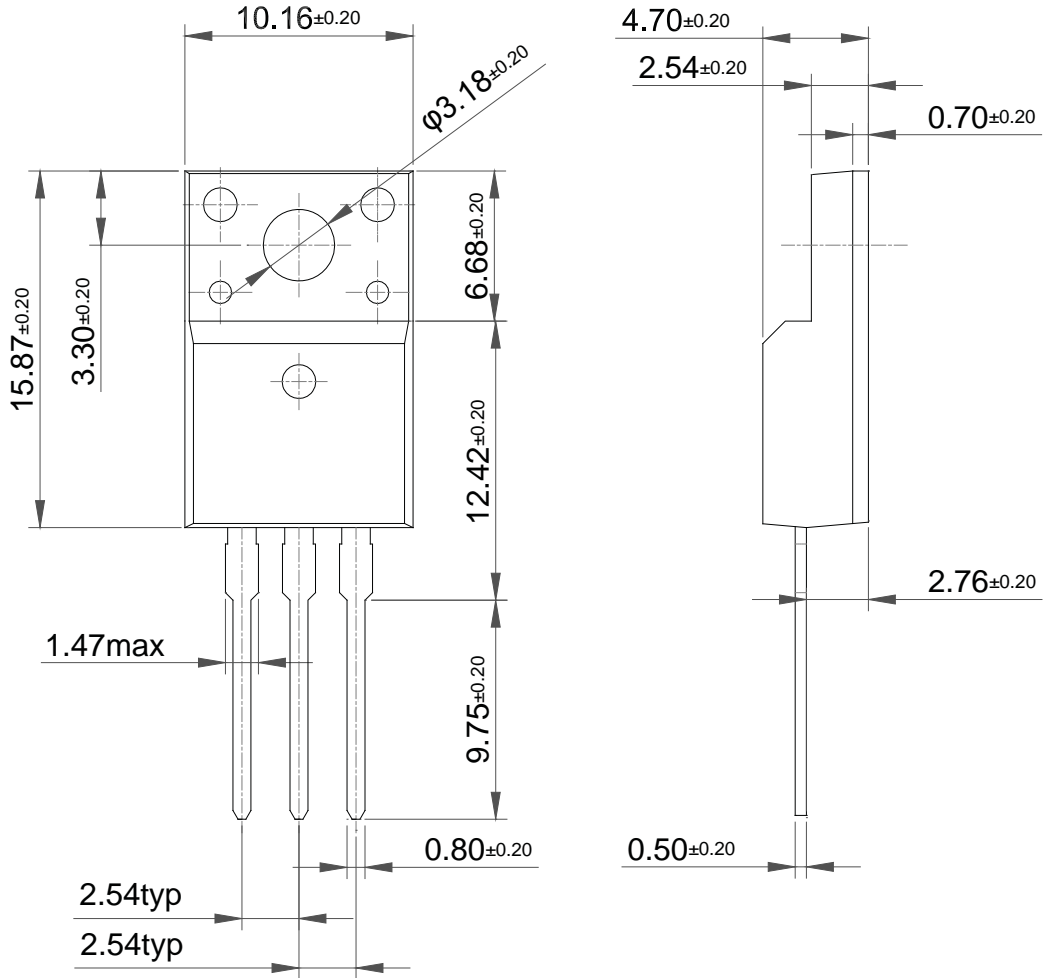


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



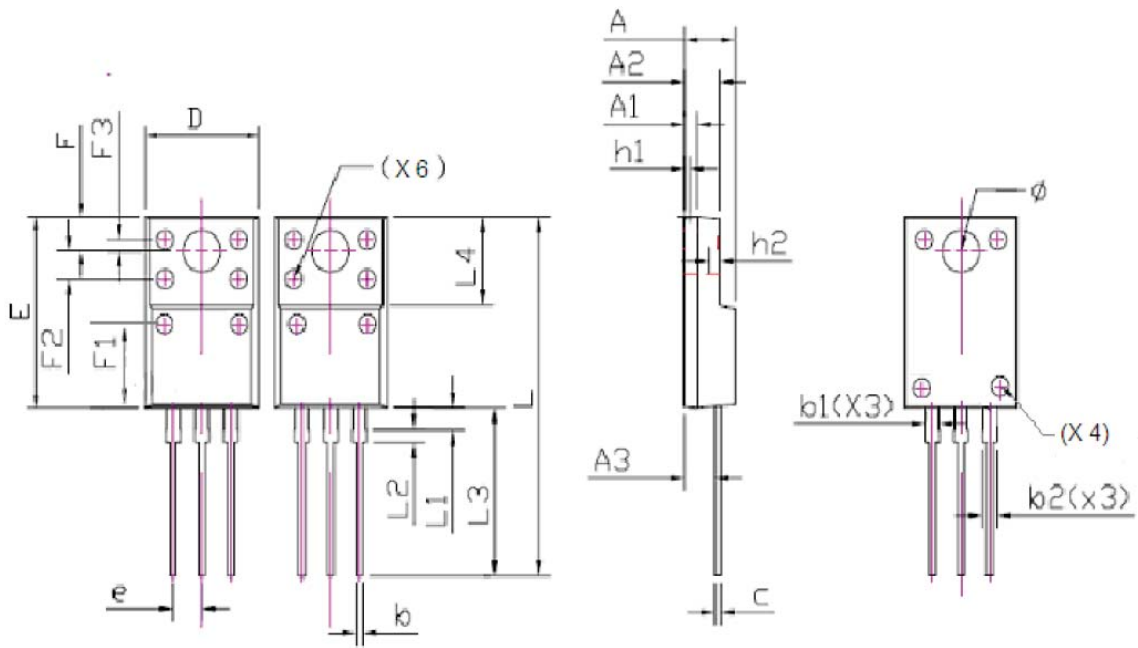
Package Dimension

TO-220F (A)



Package Dimension

TO-220F (B)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.300	0.110	0.130
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.150	1.300	0.045	0.051
b2	1.150	1.400	0.045	0.055
c	0.500	0.750	0.020	0.030
D	9.900	10.360	0.390	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
F1	6.300 REF.		0.248 REF.	
F2	2.200 REF.		0.087 REF.	
F3	0.900 REF.		0.035 REF.	
Φ	3.200	3.500	0.126	0.138
h1	0.500 REF.		0.020 REF.	
h2	0.800 REF.		0.031 REF.	
L	28.000	29.000	1.102	1.142
L1	1.400	1.800	0.055	0.071
L2	1.200	2.000	0.047	0.079
L3	13.0	13.8	0.512	0.543
L4	7.000 REF.		0.276 REF.	